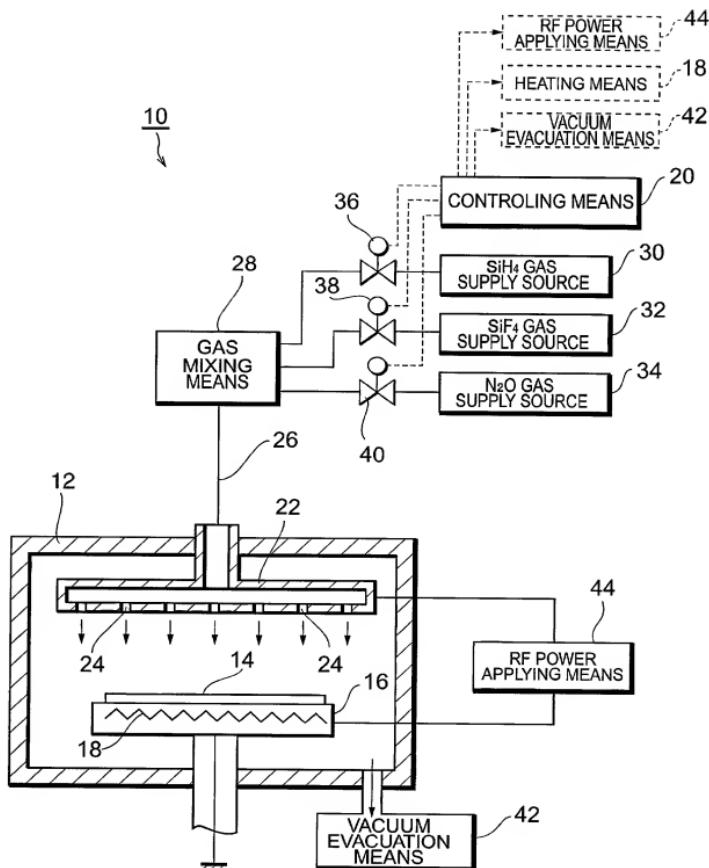
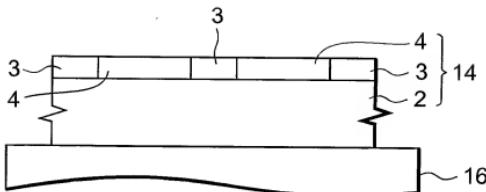


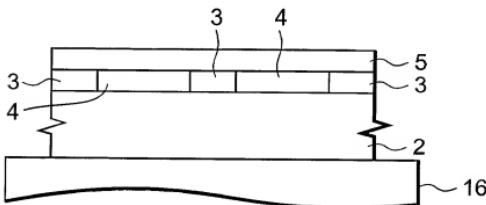
**Fig. 1**



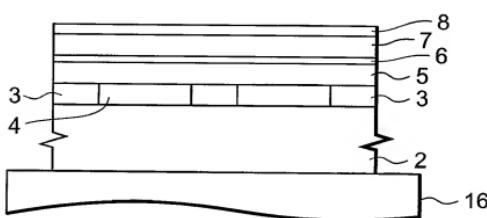
**Fig. 2A**



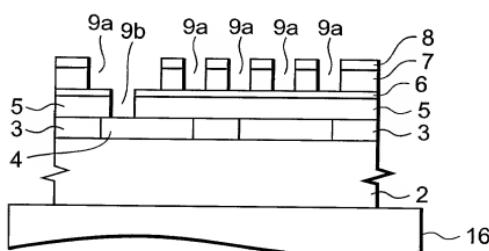
**Fig. 2B**



**Fig. 2C**



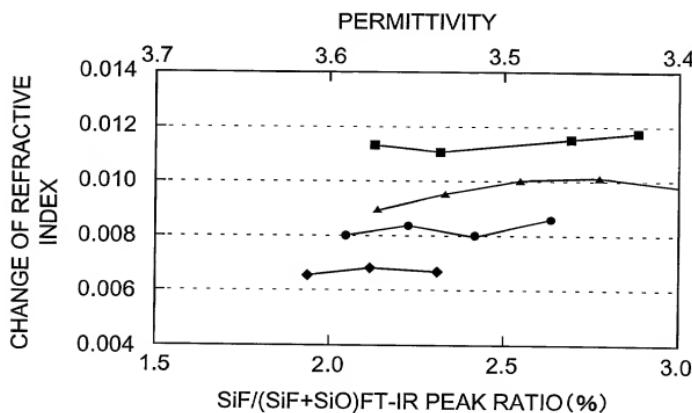
**Fig. 2D**



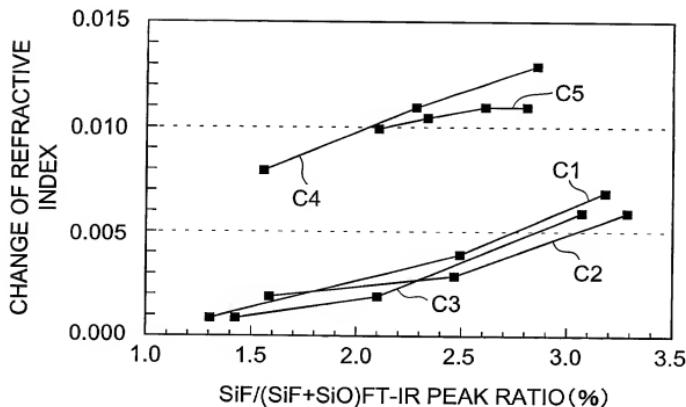
**Fig.3**

PARAMETER	TEST CONDITIONS	RAUGE OF VARIATION
13.56MHz RF POWER (W)	1500	1200~2000
PARALLEL PLATE ELECTRODE SEPARATION (cm)	1.0	1.0~1.75
CHAMBER PRESSURE (Pa)	493 (3.7Torr)	493~666 (3.7~5.0Torr)
TOTAL FLOW VOLUME(%)	100	100~200
N <sub>2</sub> O FLOW VOLUME (sccm)	1500	1500~3000
SiH <sub>4</sub> FLOW VOLUME (sccm)	115	115
SiF <sub>4</sub> FLOW VOLUME (sccm)	130	50~250

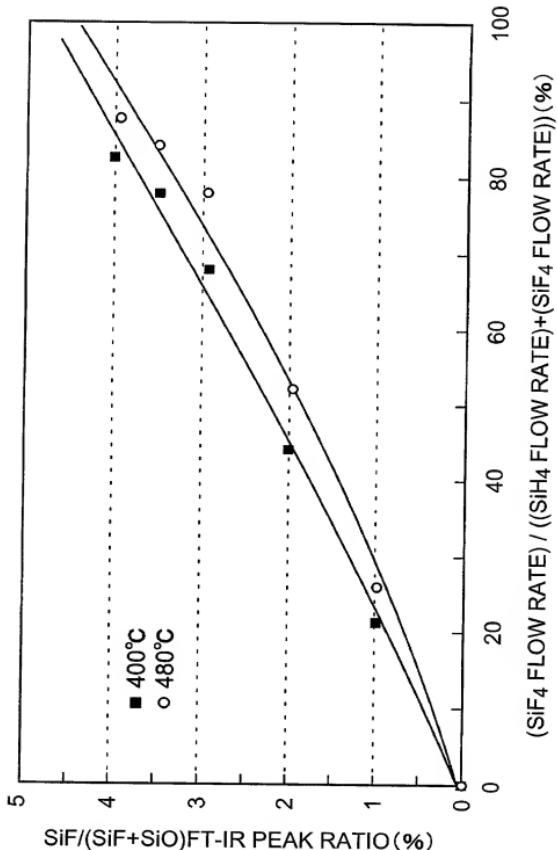
**Fig.4**



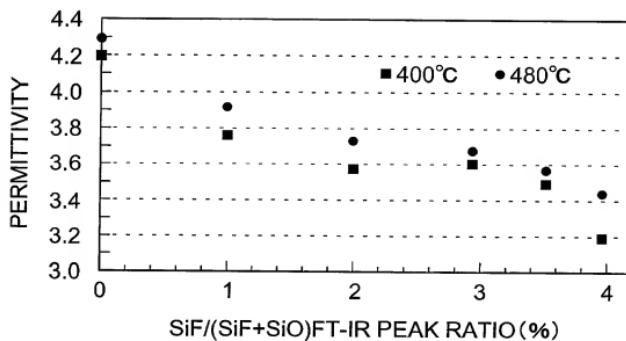
**Fig.5**



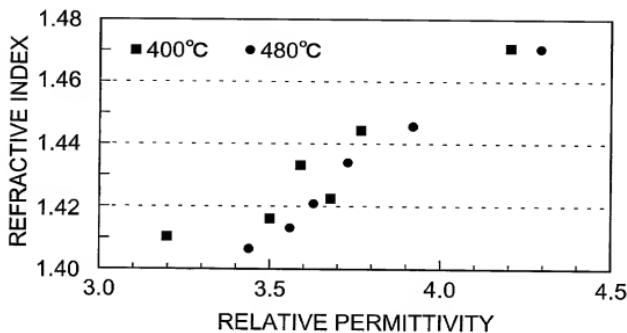
**Fig.6**



**Fig.7**



**Fig.8**

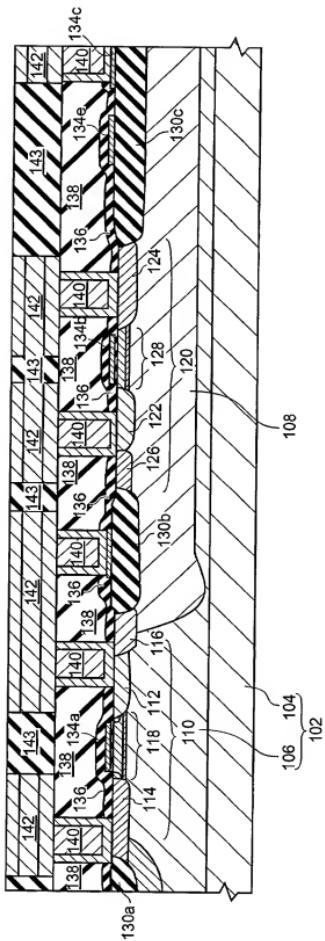


## Fig.9

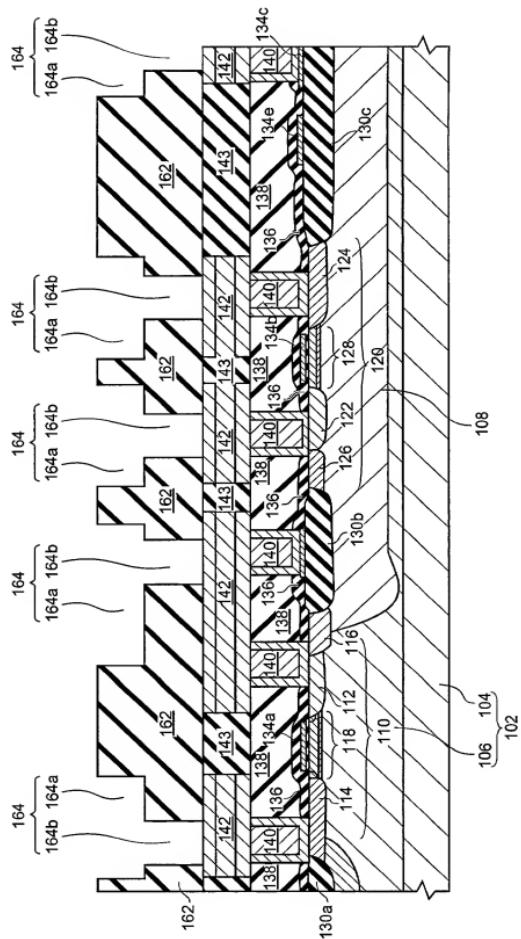
TYPE OF FILM		SiH <sub>4</sub> FSG		TEOS FSG	
FILM FORMING TEMPERAFURE		400°C	440°C	480°C	480°C
(SIOH+HOH)/SIO PEAK RATIO IN FT-IR AFTER LEFT IN CLEAN ROOM	LEFT FOR ONE WEEK	0.5	0.4	1.0	2.5
	LEFT FOR TWO WEEKS	0.7	1.1	0.7	—

100-90-80-70-60-50-40-30-20-10

*Fig. 10*



**Fig.11**



*Fig. 12*

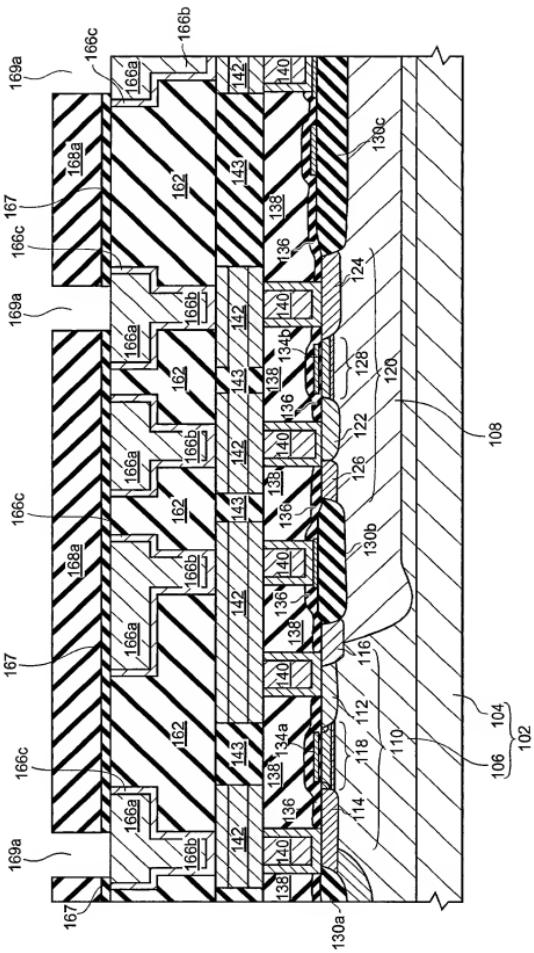


Fig. 13

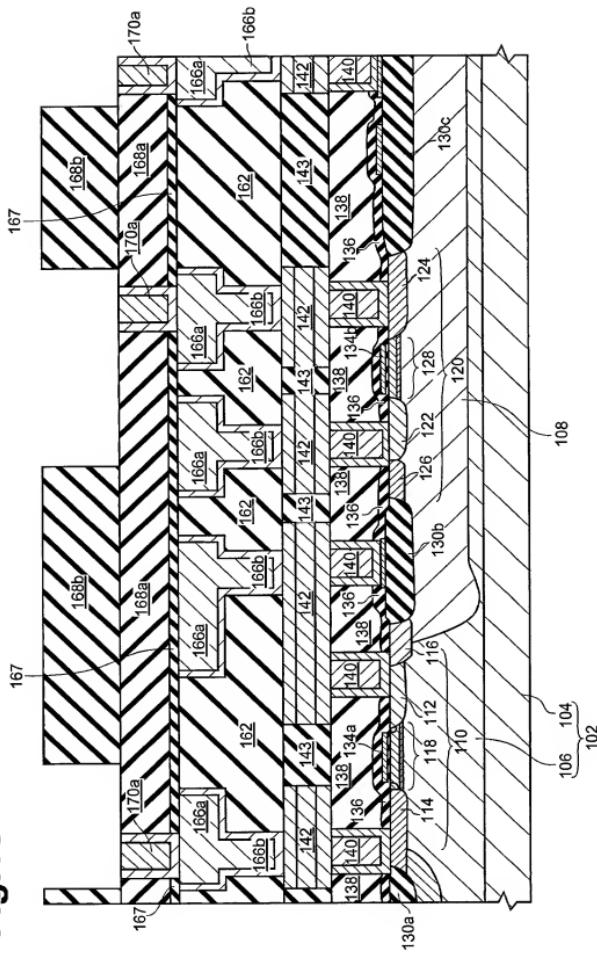


Fig. 14

